

ABSTRACT OF THE DISCLOSURE

A novel structure of an active electro-optical device is disclosed. The device is provided with complementary thin film insulated gate field effect transistors (TFTs) therein which comprise a P-TFT and an N-TFT. P-TFT and N-TFT are connected to a common signal line by the gate electrodes thereof, while the source (or drain) electrodes thereof are connected to a common signal line as well as to one of the picture element electrodes.

In case of driving the active electro-optical device, a gradation display can be carried out in a driving method having a display timing determined in relation to a time T for writing one screen and a time (t) for writing in one picture element, by applying a reference signal in a cycle of the time (t) , to the signal line used for a certain picture element driving selection, and by applying the select signal to the other signal line at a certain timing within the time (t) , and whereby setting the value of the voltage to be applied to a liquid crystal.

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